

PUMD6H

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

22 March 2021

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH7H PNP/PNP complement: PUMB3H

2. Features and benefits

- 100 mA output current capability
- Built-in resistors
- Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs
- High-temperature applications up to 175 °C

3. Applications

- Digital applications
- Cost saving alternative for BC847 / BC857 series in digital applications
- · Controlling IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1	T _{amb} = 25 °C	[1]	3.3	4.7	6.1	kΩ

[1] See section "Test information" for resistor calculation and test conditions



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	□6 □5 □4	O1 I2 GND2
2	I 1	input (base) TR1		
3	O2	output (collector) TR2		R1 R
4	GND2	GND (emitter) TR2	H ₁ H ₂ H ₃	TR1
5	12	input (base) TR2	TSSOP6 (SOT363)	R1 R1
6	01	output (collector) TR1		GND1 I1 O2
				006aaa269

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PUMD6H	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD6H	7G%

[1] % = placeholder for manufacturing site code

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

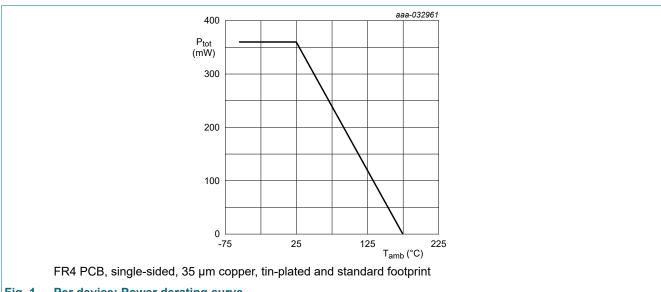
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
Per transistor, for the PNP transistor with negative polarity							
V _{CBO}	collector-base voltage	open emitter		-	50	V	
V_{CEO}	collector-emitter voltage	open base		-	50	V	
V_{EBO}	emitter-base voltage	open collector		-	7	V	
V _I	input voltage			-7	30	V	
Io	output current			-	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	240	mW	
Per device							
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW	
Tj	junction temperature			-	175	°C	
T _{amb}	ambient temperature			-55	175	°C	
T _{stg}	storage temperature			-65	175	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						'
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	230	K/W
Per device	'				-	1	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

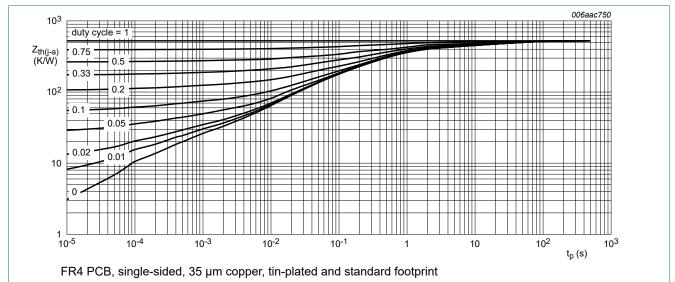


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

10. Characteristics

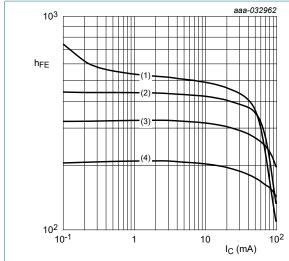
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor, for the PNP transistor v	vith negative polarity					
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{CEO} collector-emitter cut-of	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	100	nA
	current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}; T_{amb} = 25 \text{ °C}$		200	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	585	500	mV
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		1.3	0.88	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	3.3	4.7	6.1	kΩ
TR1 (NPN)				·	·	·	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
TR2 (PNP)			•		·		
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz

^[1] See section "Test information" for resistor calculation and test conditions

^[2] Characteristics of built-in transistor

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open



 $V_{CE} = 5 V$

 $(1) T_{amb} = 175 °C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) $T_{amb} = 25 ^{\circ}C$ (4) $T_{amb} = -40 ^{\circ}C$

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values

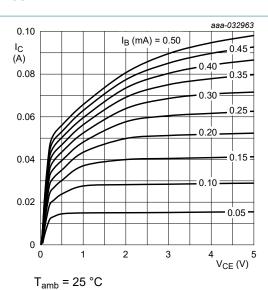
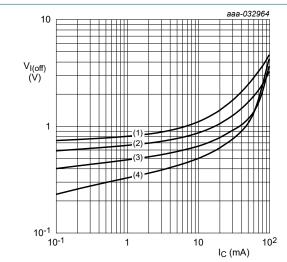


Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



 $V_{CE} = 5 V$

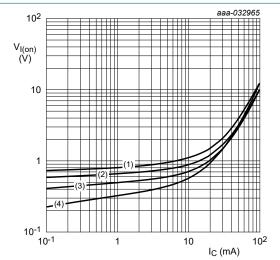
(1) $T_{amb} = -40 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

(4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 5. TR1 (NPN): Off-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 0.3 V$

 $(1) T_{amb} = -40 °C$

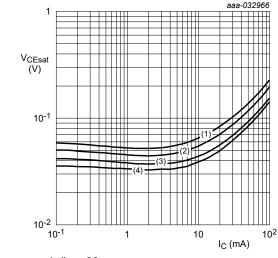
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

(4) $T_{amb} = 175 \, ^{\circ}C$

TR1 (NPN): On-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

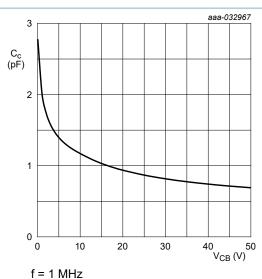


 $I_{\rm C}/I_{\rm B} = 20$

(1) T_{amb} = 175 °C (2) T_{amb} = 100 °C

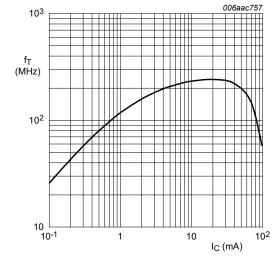
(3) $T_{amb} = 25 ^{\circ}C$ (4) $T_{amb} = -40 ^{\circ}C$

TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

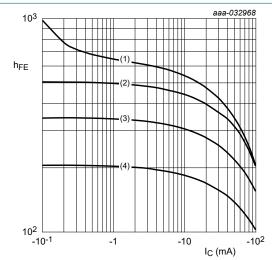


f = 100 MHz

 $T_{amb} = 25 \, ^{\circ}C$

 $V_{CE} = 5 V$

Fig. 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 V_{CE} = -5 V

 $(1) T_{amb} = 175 °C$

(2) $T_{amb} = 100 \, ^{\circ}C$

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): DC current gain as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

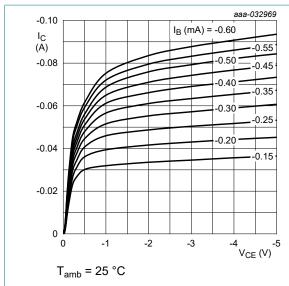
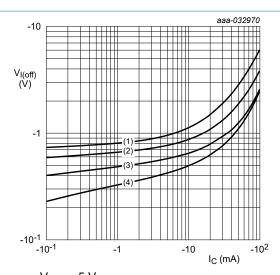
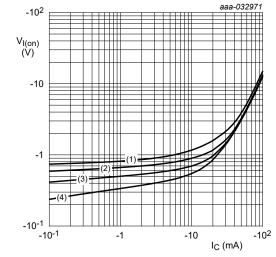


Fig. 11. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



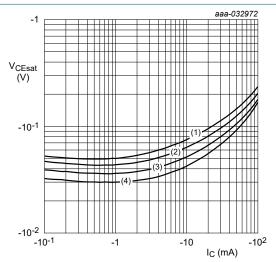
 $V_{CE} = -5 V$ (1) $T_{amb} = -40 \, ^{\circ}C$ $(2) T_{amb} = 25 °C$ $(3) T_{amb} = 100 °C$ (4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $V_{CE} = -0.3 \text{ V}$ (1) $T_{amb} = -40 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) $T_{amb} = 100 \, ^{\circ}C$ (4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 13. TR2 (PNP): On-state input voltage as a function | Fig. 14. TR2 (PNP): Collector-emitter saturation voltage of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = 175 \, ^{\circ}C$ (2) $T_{amb} = 100 \, ^{\circ}C$ (3) $T_{amb} = 25 \, ^{\circ}C$ (4) $T_{amb} = -40 \, ^{\circ}C$

as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

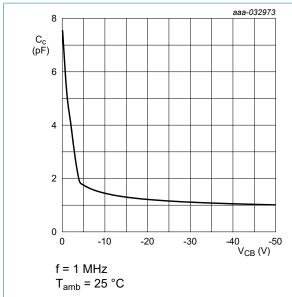


Fig. 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

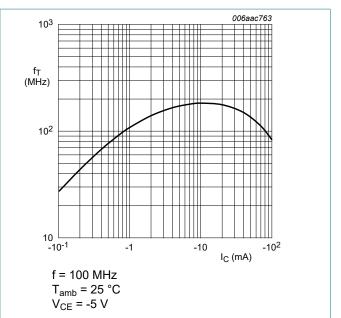


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

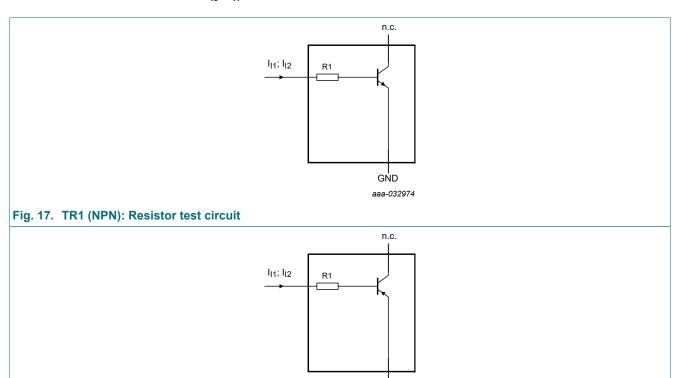
50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

11. Test information

Resistor calculation

• Calculation of bias resistor 1 (R1)

$$R_I = \frac{V(I_{I2}) - V(I_{II})}{I_{I2} - I_{II}}$$



Resistor test conditions

Table 8. Resistor test conditions

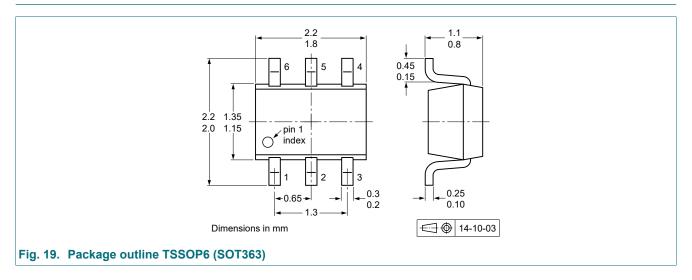
Fig. 18. TR2 (PNP): Resistor test circuit

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁₁	I _{I2}		
Per transistor, for the PNP transistor with negative polarity						
PUMD6H	4.7	open	600 μΑ	700 μΑ		

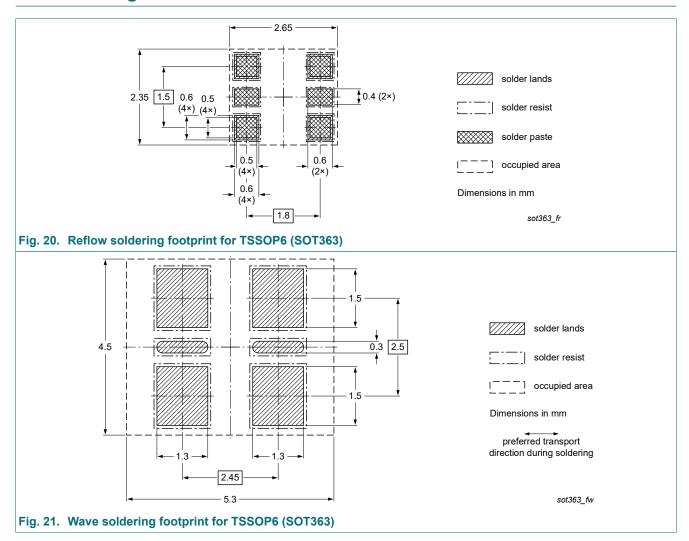
GND aaa-032975

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

12. Package outline



13. Soldering



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

14. Revision history

Table 9. Revision history

Data sheet ID	Release date		Change notice	Supersedes
PUMD6H v.1	20210322	Product data sheet	-	-

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 4.7 k Ω , R2 = open

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Contents

1. General description	
2. Features and benefits	
3. Applications	
4. Quick reference data	
5. Pinning information	2
6. Ordering information	2
7. Marking	
8. Limiting values	
9. Thermal characteristics	
10. Characteristics	5
11. Test information	
12. Package outline	11
13. Soldering	
14. Revision history	12
15. Legal information	
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